

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	453	(bicmos) and (collector or base or gate) near8 (sige or sigec or si near ge or silicon near germanium or gesi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 09:16
S2	217	(bicmos) and (collector or base or gate) near8 (sige or sigec or si near ge or silicon near germanium or gesi) and (poly or polycrystal or polycrystalline or poly near crystalline) near4 (base or gate or sige or si near ge or silicon near germanium or sigec or gesi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:58
S3	0	(bjt or hbt) same (collector or base) near5 (sige or si near ge or gesi or sigec or silicon near germanium) near10 (single near crystal\$4 or monocrystal\$4) and gate near10 (sige or si near ge or gesi or sigec or silicon near germanium) near10 (polycrystal\$4 or poly near crystal\$4 or poly)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:55
S4	3	(bjt or hbt or bicmos) and (collector or base) near15 (sige or si near ge or gesi or sigec or silicon near germanium) near15 (single near crystal\$4 or monocrystal\$4) and gate near15 (sige or si near ge or gesi or sigec or silicon near germanium) near15 (polycrystal\$4 or poly near crystal\$4 or poly)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:56
S5	50	(bicmos) and (collector or base or gate) near8 (sige or sigec or si near ge or silicon near germanium or gesi) and (poly or polycrystal or polycrystalline or poly near crystalline) near4 (gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:58
S6	33	(bicmos) and (collector or base) near8 (sige or sigec or si near ge or silicon near germanium or gesi) and (poly or polycrystal or polycrystalline or poly near crystalline) near4 (gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:58
S7	3	("5304501"   "6117717"   "6667202").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/23 11:16
S9	1	"6346453".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/23 11:23
S10	1	"6552374".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/23 11:24
S11	182	(bicmos or hbt) and (single near crystal\$4 or monocrystal\$4) near4 (sige or gesi or sigec or silicon near germanium or si near ge) and (polycrystal\$4 or poly or poly near crystal\$4) near4 (sige or gesi or silicon near germanium or si near ge)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 11:25
S12	24	(bicmos or hbt) and (single near crystal\$4 or monocrystal\$4) near4 (sige or gesi or sigec or silicon near germanium or si near ge) and (polycrystal\$4 or poly or poly near crystal\$4) near4 (sige or gesi or silicon near germanium or si near ge) and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 11:26
S13	118	257/190.cor.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 12:34
S14	384	257/192.cor.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 12:43

S15	95	257/192.cor. and (sige or sigec or gesi or silicon near germanium or si near ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 12:43
S16	32	257/195.cor.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 12:47
S17	386	257/197.cor.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 13:23
S18	8	(US-20030155611-\$ or US-20050048745-\$).did. or (US-5356821-\$ or US-6346453-\$ or US-6563147-\$ or US-6723610-\$ or US-6746928-\$ or US-6900115-\$).did.	US-PGPUB; USPAT	OR	ON	2005/09/23 13:14
S19	21	257/201.cor.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 13:26
S20	137	257/378.cor.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 13:38
S21	73	257/577.cor.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 13:46
S22	65	257/588.cor.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 13:52
S23	5	(hbt or bicmos) and (collector) near6 (opening or aperture or hole) near10 (monocrystal\$4 or single near crystal\$4) near10 (sige or gesi or sigec or si near ge or silicon near germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 13:53